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(54) **SEMICONDUCTOR MEMORY DEVICE AND METHOD OF MANUFACTURING THE SAME**

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ABSTRACT

A semiconductor memory device includes a substrate including first and second surfaces opposite to each other, a first active pattern on the first surface, a first channel pattern on the first active pattern and a first source/drain pattern connected to the first channel pattern, a gate electrode provided on the first channel pattern and extending in a first direction, the gate electrode adjacent to the first source/drain pattern in a second direction intersecting the first direction, a shared contact provided under the first source/drain pattern and the gate electrode and electrically connecting the first source/drain pattern and the gate electrode to each other, and a backside metal layer on the second surface.

